AUTOMOTIVE

RoHS

COMPLIANT HALOGEN

FREE



### Vishay Semiconductors

# Hyperfast Rectifier, 3 A FRED Pt®



### LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	3 A			
$V_{R}$	100 V			
V <sub>F</sub> at I <sub>F</sub>	0.69 V			
t <sub>rr</sub>	25 ns			
T <sub>J</sub> max.	175 °C			
Package	SMC (DO-214AB)			
Circuit configuration	Single			

#### **FEATURES**

- Hyperfast recovery time, reduced Q<sub>rr</sub>, and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- · Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, piezo-injection, as high frequency rectifiers, and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

### **MECHANICAL DATA**

Case: SMC (DO-214AB)

Molding compound meets UL 94 V-0 flammability rating **Terminals:** matte tin plated leads, solderable per

J-STD-002

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	$V_{RRM}$		100	V
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>Sp</sub> = 142 °C	3	۸
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C, 6 ms square pulse	130	A
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	$V_{BR}$ , $V_{R}$	I <sub>R</sub> = 100 μA	100	-	-		
Converd valtage ner diede		I <sub>F</sub> = 3 A	-	0.83	0.90	V	
Forward voltage, per diode	V <sub>F</sub>	I <sub>F</sub> = 3 A, T <sub>J</sub> = 125 °C	-	0.69	0.75		
Reverse leakage current, per diode		$V_R = V_R$ rated	-	-	2	μA	
neverse leakage current, per diode	I <sub>R</sub>	$T_J = 125 ^{\circ}\text{C},  V_R = V_R  \text{rated}$	-	1	10	μΑ	
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 100 V	-	23	-	pF	



# Vishay Semiconductors

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 \text{ A}, dI_F/dt = 50$	A/μs, V <sub>R</sub> = 30 V	-	27	-	
Dayawa waasyaw tima		$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$		-	-	25	
Reverse recovery time t <sub>rr</sub>	Lrr	T <sub>J</sub> = 25 °C		-	18	-	ns
		T <sub>J</sub> = 125 °C		-	30	-	
Peak recovery current I <sub>RRM</sub>		T <sub>J</sub> = 25 °C	$I_F = 3 \text{ A},$ $dI_F/dt = 200 \text{ A/}\mu\text{s},$ $V_R = 100 \text{ V}$	-	2.1	-	^
	IRRM	T <sub>J</sub> = 125 °C		-	4	-	A
Reverse recovery charge		T <sub>J</sub> = 25 °C		-	19	-	nC
	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	60	-	110

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C
Thermal resistance, junction to mount	R <sub>thJM</sub>	Device mounted on PCB with 2 x 3.5 mm soldering lands	-	7.7	14	°C/W
Approximate weight				0.24		g
Approximate weight			·	0.008		oz.
Marking device		Case style SMC (DO-214AB)		31	<del>-</del> 11	

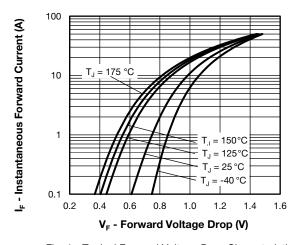


Fig. 1 - Typical Forward Voltage Drop Characteristics

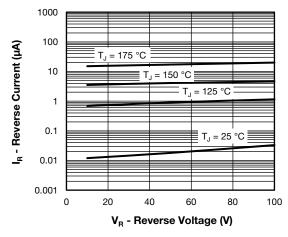


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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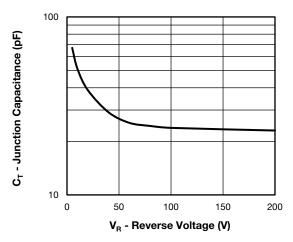


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

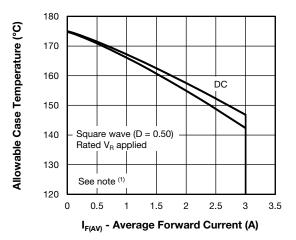


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

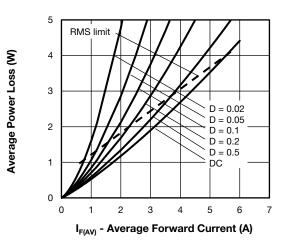


Fig. 5 - Forward Power Loss Characteristics

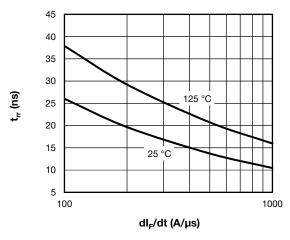


Fig. 6 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

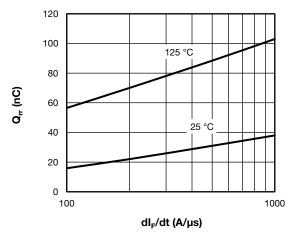
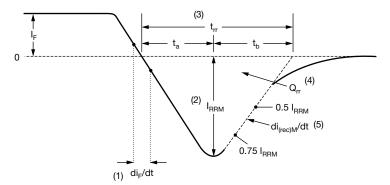


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

### Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 5)}; \\ Pd_{REV} = \text{inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = \text{rated } V_R \\ \end{array}$ 

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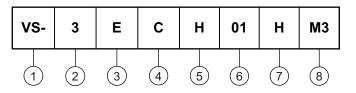


- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (4)  $\rm Q_{rr}$  area under curve defined by  $\rm t_{rr}$  and  $\rm I_{RRM}$
- (2) I<sub>RRM</sub> peak reverse recovery current
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (5) di<sub>(rec)M</sub>/dt peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 8 - Reverse Recovery Waveform and Definitions

### **ORDERING INFORMATION TABLE**

### Device code



- 1 Vishay Semiconductors product
- 2 Current code (3 = 3 A)
- 3 Circuit configuration:

E = single diode

- 4 C = SMC package
- 5 Process type,

H = hyperfast recovery

- 6 Voltage code (01 = 100 V)
- 7 H = AEC-Q101 qualified
- M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-3ECH01HM3/9AT	3500	3500	13"diameter plastic tape and reel			

LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95402</u>					
Part marking information <u>www.vishay.com/doc?95472</u>					
Packaging information	www.vishay.com/doc?95404				

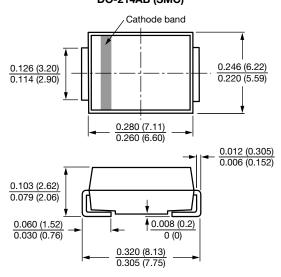


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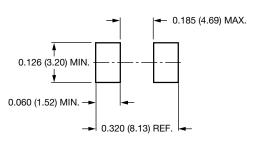
## **SMC**

### **DIMENSIONS** in inches (millimeters)

### DO-214AB (SMC)



### Mounting Pad Layout





## **Legal Disclaimer Notice**

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